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Indirect-to-direct band gap transition and optical properties of metal alloys of $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$: a theoretical study

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In recent years, double perovskites have attracted considerable attention as potential candidates for photovoltaic applications. However, most double perovskites are not suitable for single-junction solar cells due to their large band gaps (over 2.0 eV). In the present study, we have investigated the structural, mechanical, electronic and optical properties of the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions using first-principles calculations based on density functional theory. These compounds exhibit good structural stability compared to $\text{CH}_3\text{NH}_3\text{PbI}_3$. The results suggest that Cs_2TeI_6 is an indirect band gap semiconductor, and it can become a direct band gap semiconductor with the value of 1.09 eV when the doping concentration of Ti^{4+} is 0.50. Moreover, an ideal direct band gap of 1.31 eV is obtained for $\text{Cs}_2\text{Te}_{0.75}\text{Ti}_{0.25}\text{I}_6$. The calculated results indicate that all the structures are ductile materials except for $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$. Our results also show that these materials possess large absorption coefficients in the visible light region. Our work can provide a route to explore stable, environmentally friendly and high-efficiency light absorbers for use in optoelectronic applications.

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1. Introduction

Lead-based halide perovskites have attracted great attention for optoelectronic applications in the past ten years.^{1–3} The power conversion efficiency (PCE) of lead-based halide perovskite solar cells increased to a high value of 25.2% in 2019.⁴ However, the toxicity of lead and poor stability still remain significant challenges for commercial applications. Extensive efforts have been paid to exploring lead-free or lead-less and stable halide perovskite materials for solar cells. Sn^{2+} and Ge^{2+} metal ions have been expected to replace Pb^{2+} ions in perovskites.^{5–9} Sn^{2+} ion is highly unstable and can be easily oxidized to Sn^{4+} ,¹⁰ which results in decreased photovoltaic performance. To date, the highest PCE of Ge-based halide perovskites is only 4.94%.¹¹ Two dimensional (2D) layered perovskites have been also explored such as $\text{A}_3\text{B}_2\text{X}_9$ ($\text{A} = \text{Cs}, \text{Rb}$; $\text{B} = \text{Bi}, \text{Sb}$; $\text{X} = \text{I}, \text{Br}, \text{Cl}$).^{12–17} However, these materials have large band gaps over 2.0 eV, which are not suitable for perovskite solar cells.

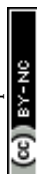
In recent years, halide double perovskites $\text{A}_2\text{B}^+\text{B}^{3+}\text{X}_6$ have been developed as stable and non-toxic alternatives to lead-based perovskite materials, where two toxic lead ions are substituted by using monovalent B^+ and trivalent B^{3+} , such as Ag^+ , Bi^{3+} , and Sb^{3+} . Although most of the reported double perovskites show excellent stability, their band gaps are too large for application in single-junction solar cells.^{18–21} A low band gap (1.66 eV) of double perovskites $\text{Cs}_2\text{NaBiI}_6$ has been synthesized, which possesses excellent stability and strong light absorption performance.²² However, its PCE is only 0.42%, which is much lower than those of lead-based hybrid perovskites.

The vacancy-ordered double perovskites with formula of A_2BX_6 can be regarded as a derivative structure of the traditional ABX_3 , where two toxic lead ions are substituted by one tetravalent ion to keep charge conservation as the conventional perovskites. Cs_2SnI_6 is one of the most representative perovskite materials, which belongs to a cubic structure with space group $\text{Fm}\bar{3}m$.²³ The previous study classified Cs_2SnI_6 as zero dimensional (0D) structure.²⁴ However, this compound still maintains three dimensional (3D) structure and presents 3D materials' properties, so it is still considered as 3D material.²⁵ Cs_2SnI_6 exhibits air and moisture stability, and strong visible light absorption, which are advantageous properties for photovoltaic applications.^{26,27} The first tested solar cell using Cs_2SnI_6 as absorber material in air showed a small PCE of 0.96%.²⁶ Meanwhile, MA_2SnI_6 was found to have a direct band gap of 1.81 eV with a strong absorption coefficient of $\sim 7 \times 10^4 \text{ cm}^{-1}$.²⁸

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In this work, the structural stability, mechanical properties, electronic and optical properties of double perovskites $\text{Cs}_2\text{-Te}_{1-x}\text{Ti}_x\text{I}_6$ were investigated for the first time. The results show that $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$ has excellent stability, suitable direct band gap, and strong optical absorption, which is a promising candidate material for optoelectronic device. The mechanical properties of these materials are discussed in detail, and the results indicate that they are ductile materials except for $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$.

$U = 2$ eV was finally chosen for the electronic and optical calculations for the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions.

3.1 Structure properties

The crystal structures of both Cs_2TeI_6 and Cs_2TiI_6 belong to the cubic phase with space group $Fm\bar{3}m$.^{29,30} The calculated lattice constant of Cs_2TeI_6 is 11.66 Å, which is in good agreement with experimental value (11.71 Å).²⁹ The corresponding lattice constant of Cs_2TiI_6 is predicted to be 11.38 Å, which is much lower than its experimental value (11.67 Å).³⁰ The ion radii of Te^{4+} and Ti^{4+} are 0.97 Å and 0.61 Å, respectively. Interestingly, the experimental lattice constants of Cs_2TeI_6 and Cs_2TiI_6 are almost the same. It should be noted that the lattice parameter of Cs_2TiI_6 is estimated to be 11.67 Å according to the experimental XRD results. The optimized structures of the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions are depicted in Fig. 1. x is the concentration of Ti^{4+} . The x values of 0.00, 0.25, 0.50, 0.75, and 1.00 are adopted in this study. For the species with $x = 0.25, 0.50$, and 0.75 , all the possible arrangements are considered in this work. The results show that different structures with the same doping percentage

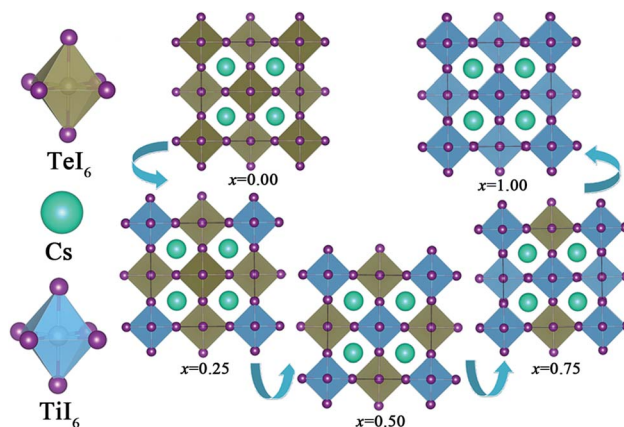


Fig. 1 The optimized structures of the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions.

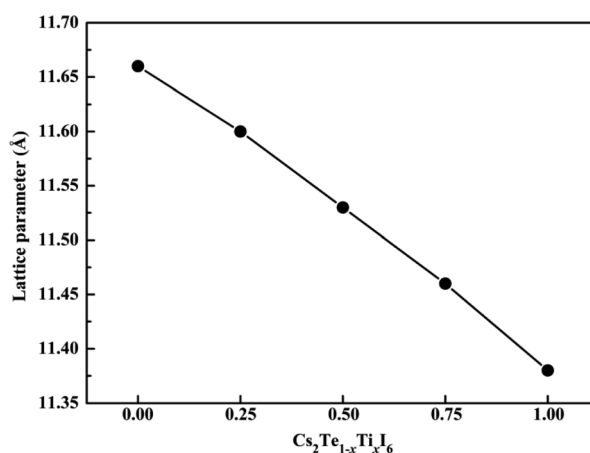


Fig. 2 The lattice constants of the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions.

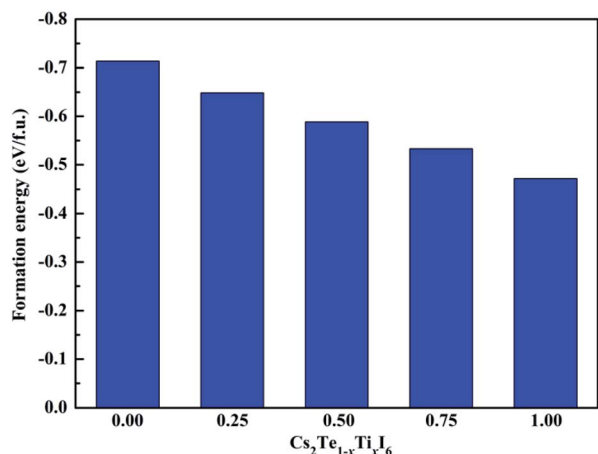


Fig. 3 Calculated formation energies of the Cs₂Te_{1-x}Ti_xI₆ solid solutions.

have the same stability, with calculated energy differences within less than 2 meV. The lattice constant of Cs₂Te_{1-x}Ti_xI₆ decreases gradually when the concentration of Ti⁴⁺, as shown in Fig. 2. Moreover, the bond length Te–I (2.96 Å) of Cs₂TeI₆ is larger than the bond length Ti–I (2.76 Å) of Cs₂TiI₆.

The tolerance factor (t) has been widely used to predict the structural stability of perovskite material. The formula is defined as follows:⁴⁴

$$t = \frac{R_A + R_X}{\sqrt{2}(R_B + R_X)} \quad (1)$$

where R_A , R_B , and R_X are the effective ionic radii for A, B, and X, respectively. In general, the perovskite structure is stable when the t value is in the range of 0.81–1.11.⁴⁵ Our calculated values of t are 0.86 and 0.97 for Cs₂TeI₆ and Cs₂TiI₆, respectively. These

results confirm that the substitution of Ti⁴⁺ for Te⁴⁺ in Cs₂TeI₆ is feasible. To further assess the thermodynamic stability of the Cs₂Te_{1-x}Ti_xI₆ solid solutions, we have calculated their formation energies. The formation energy can be obtained according to the following equation:

$$\Delta H = \Delta E(\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6) - 2\Delta E(\text{CsI}) - (1-x)\Delta E(\text{TeI}_4) - x\Delta E(\text{TiI}_4) \quad (2)$$

where $E(\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6)$, $E(\text{CsI})$, $E(\text{TeI}_4)$, and $E(\text{TiI}_4)$ are the total energy of Cs₂Te_{1-x}Ti_xI₆, CsI, TeI₄, and TiI₄, respectively. The calculated formation energies of the Cs₂Te_{1-x}Ti_xI₆ solid solutions are demonstrated in Fig. 3. Our calculated result shows that the ΔH value of MAPbI₃ is 0.01 eV per f.u., which is in good agreement with the previous reported data.⁴⁶ These results indicate that MAPbI₃ is marginally stable. It can be seen that all the compounds exhibit good stability with larger negative ΔH values compared to MAPbI₃. Moreover, it is observed that the structural stability of Cs₂Te_{1-x}Ti_xI₆ decreases gradually with the increasing concentration of Ti⁴⁺. In addition, the phonon spectrum of the mixed-metal double perovskites are also studied. As shown in Fig. 4, it can be seen that none of the imaginary phonon mode exists for Cs₂Te_{0.75}Ti_{0.25}I₆ and Cs₂Te_{0.50}Ti_{0.50}I₆, which indicate that they are kinetically stable. Interestingly, Cs₂Te_{0.50}Ti_{0.50}I₆ has very small imaginary frequencies. According to the previous study,⁴⁷ all small imaginary frequencies will disappear when it is at room temperature. Therefore, Cs₂Te_{0.50}Ti_{0.50}I₆ is considered to be a stable structure at room temperature.

3.2 Mechanical properties

To predict the mechanical stability of double perovskite Cs₂Te_{1-x}Ti_xI₆, the corresponding elastic constants were calculated

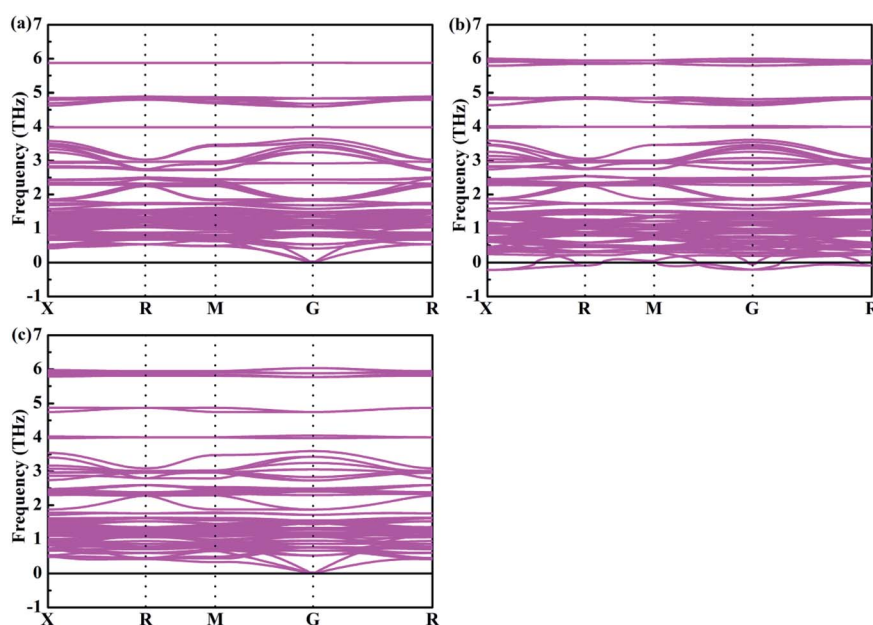


Fig. 4 Phonon spectrum of (a) Cs₂Te_{0.75}Ti_{0.25}I₆, (b) Cs₂Te_{0.50}Ti_{0.50}I₆, and (c) Cs₂Te_{0.25}Ti_{0.75}I₆.



Table 1 The calculated elastic constants C_{ij} (GPa), bulk modulus B (GPa), shear modulus G (GPa), Young's modulus (E), Pugh's ratio (B/G), and Poisson's ratio ν of $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$

	C_{11}	C_{12}	C_{44}	B	G	E	B/G	ν
Cs_2TeI_6	19.14	10.24	8.78	13.21	6.68	17.16	1.98	0.28
$\text{Cs}_2\text{Te}_{0.75}\text{Ti}_{0.25}\text{I}_6$	20.20	9.80	9.86	13.27	7.63	19.20	1.74	0.26
$\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$	17.51	8.39	9.98	11.43	7.29	18.03	1.57	0.24
$\text{Cs}_2\text{Te}_{0.25}\text{Ti}_{0.75}\text{I}_6$	19.14	11.08	10.27	13.77	7.06	18.08	1.95	0.28
Cs_2TiI_6	17.85	10.29	10.70	12.81	7.05	17.88	1.82	0.27

using the finite strain theory.⁴⁸ For cubic structure, the Born stability criteria is given as follows:⁴⁹

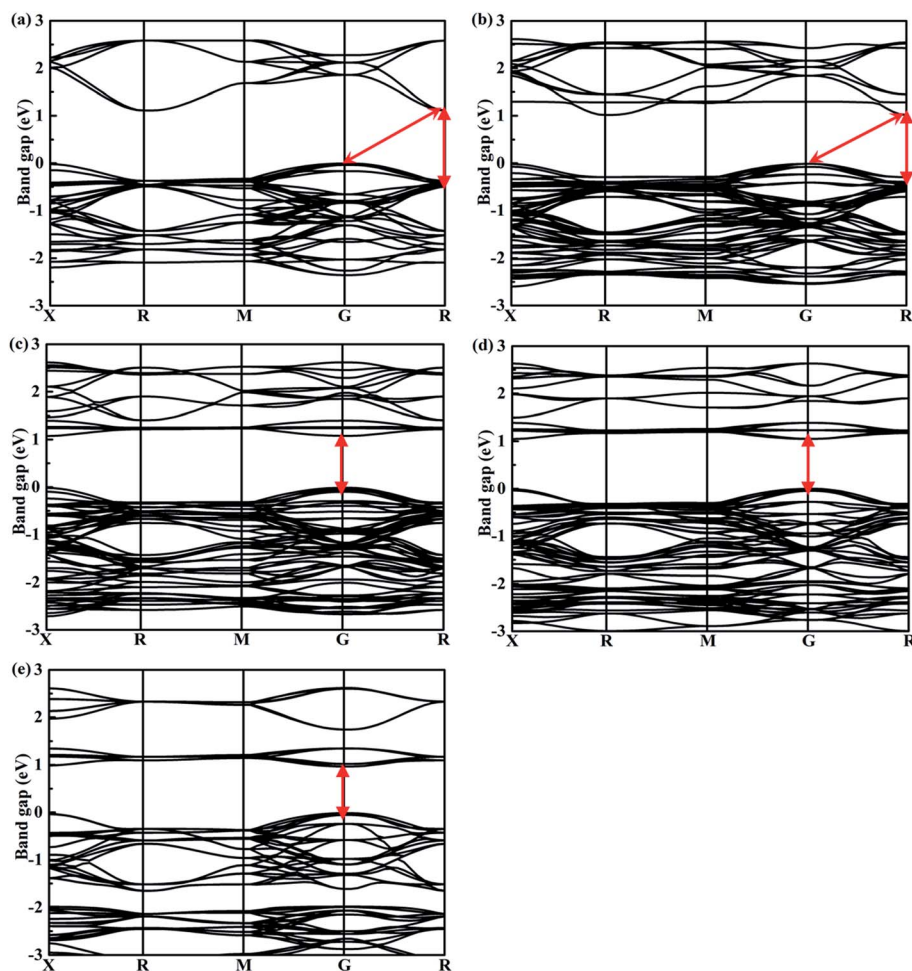
$$C_{11} - C_{12} > 0, C_{11} + 2C > 120, C_{44} > 0 \quad (3)$$

The calculated results of three independent elastic constants are listed in Table 1. All the compounds satisfy the above Born stability criteria, indicating that they are mechanical stable. The bulk modulus (B) and shear modulus (G) can be obtained by using Hill approximations.⁵⁰ The Young's modulus (E) and Poisson ratio (ν) can be calculated from the values of bulk

modulus and shear modulus by applying the following formula:⁵¹

$$E = 9BG/(3B + G), \nu = (3B - 2G)/(6B + 2G) \quad (4)$$

In order to investigate the ductility and brittleness of the studied double perovskites, we calculated the Pugh's and Poisson ratios. The Pugh's ratio is the ratio between bulk modulus and shear modulus (B/G), which is proposed by Pugh.⁵² The material is considered as ductile when the value of Pugh's ratio is larger than 1.75, otherwise it is brittle. The Poisson's ratio can also be used to separate the ductile materials from brittle materials. The ductile materials have the Poisson's ratio greater than 0.26, and it is smaller than 0.26 for brittle materials.⁵³ From Table 1, it can be seen that $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$ is a brittle material, while other four compounds are ductile materials. It should be noted that the Poisson's ratio values of the studied double perovskites are close to the required lowest limit. The smaller the value of Young's modulus, the better flexibility of a material. The results show that Young's modulus of Cs_2TeI_6 is the smallest among the five structures, which indicates that it is

**Fig. 5** Calculated band structures of double perovskites along the $X-R-M-G-R$ path for (a) Cs_2TeI_6 , (b) $\text{Cs}_2\text{Te}_{0.75}\text{Ti}_{0.25}\text{I}_6$, (c) $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$, (d) $\text{Cs}_2\text{Te}_{0.25}\text{Ti}_{0.75}\text{I}_6$, and (e) Cs_2TiI_6 .

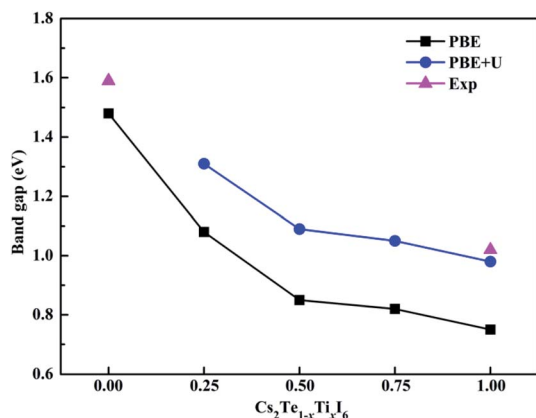


Fig. 6 Experimental and theoretical band gap trends with different methods of $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$.

the most flexible. Moreover, it is beneficial to form high quality film for ductile materials.

3.3 Electronic properties

The band structures calculated along high symmetry directions in the Brillouin zone are shown in Fig. 5. Cs_2TeI_6 has an indirect band gap between G and R point, and a direct band gap at R point. The indirect and direct band gaps of Cs_2TeI_6 are 1.12 and 1.48 eV, respectively. The previous reported band gap of Cs_2TeI_6 is about 1.5 eV,^{54,55} and the recent experimentally observed

optical gap is 1.59 eV.²⁹ The band gap of Cs_2TiI_6 with the PBE method is 0.75 eV, which is lower than its experimental value (1.02 eV).³⁰ Therefore, the DFT+U method is employed to obtain accurate band gap of Cs_2TiI_6 . The result shows that Cs_2TiI_6 possesses a direct band gap with 0.98 eV at the G point, which is in good agreement with its experimental value.³⁰ The Spin-orbit coupling (SOC) effect on the electronic structures of Te- and Ti-based perovskites is small.^{30,37} It is observed that $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$ is a direct band gap semiconductor with the value of 1.09 eV, while $\text{Cs}_2\text{Te}_{0.75}\text{Ti}_{0.25}\text{I}_6$ is an indirect band gap semiconductor. The direct band gap of $\text{Cs}_2\text{Te}_{0.25}\text{Ti}_{0.75}\text{I}_6$ is 1.05 eV. The trend in band gap is displayed in Fig. 6. The band gap of Cs_2TeI_6 reduces gradually when the ratio of Ti^{4+} increases. The band gaps of the two calculations with PBE and PBE+U show the same tendency. The variation in band gap is only 0.11 eV when the concentration of Ti^{4+} changes from 0.50 to 1.00. It should be noted that the direct band gap of Cs_2TeI_6 is close to the experimental value. The direct band gap of $\text{Cs}_2\text{Te}_{0.75}\text{Ti}_{0.25}\text{I}_6$ is 1.31 eV, which is a potential candidate for single-junction solar cells according to the Shockley–Queisser theory.⁵⁶ An indirect-to-direct band gap transition can be observed when the doping content of Ti^{4+} increases from 0.25 to 0.50. Moreover, the direct band gap is significantly reduced by 0.22 eV. It can be seen that the band gaps of the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions are apparently underestimated at the PBE method, as shown in Fig. 6.

Fig. 7 shows the calculated density of states of the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions. For Cs_2TeI_6 , the valence band maximum (VBM) is mainly contributed by the I-p orbitals, while

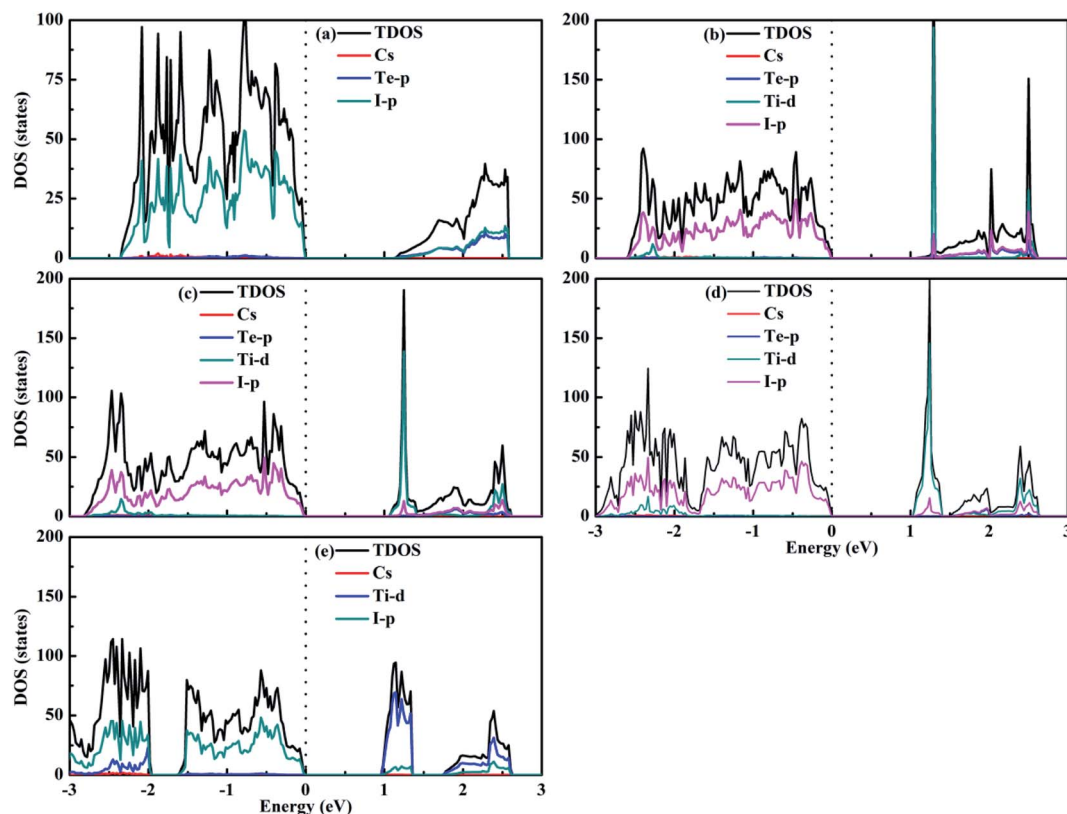


Fig. 7 Density of states of (a) Cs_2TeI_6 , (b) $\text{Cs}_2\text{Te}_{0.75}\text{Ti}_{0.25}\text{I}_6$, (c) $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$, (d) $\text{Cs}_2\text{Te}_{0.25}\text{Ti}_{0.75}\text{I}_6$, and (e) Cs_2TiI_6 .



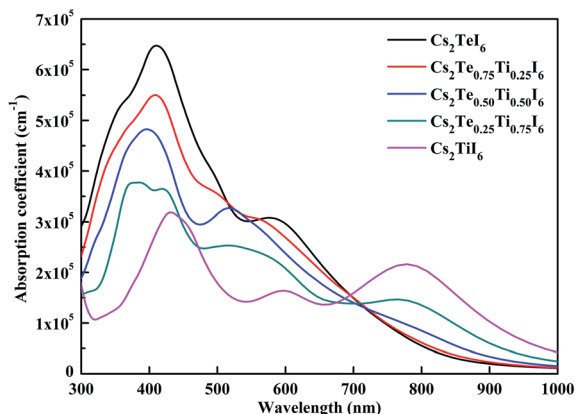


Fig. 8 The optical spectra of the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions.

the conduction band minimum (CBM) is dominated by the Te-p orbitals along with the I-p orbitals. For Cs_2TiI_6 , the VBM is mainly composed of the I-p orbitals, whereas the CBM is composed of the Ti-d orbitals. The similar situation is observed for the mixed Te-Ti double perovskites with respect to Cs_2TiI_6 . It can be seen that Cs^+ does not contribute to the band edge states.

3.4 Optical properties

The calculated optical absorption spectrum is given in Fig. 8. Cs_2TeI_6 shows a large absorption coefficient in the visible light region. The absorption coefficient of Cs_2TiI_6 is over 10^{-5} cm^{-1} in the whole region, but it is lower than that of Cs_2TeI_6 in the range of 300–700 nm. For Cs_2TiI_6 , two strong absorption peaks are located at about 450 and 800 nm, respectively. The optical absorption ability gradually increases when the proportion of Ti^{4+} decreases. In general, the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions have strong and wide optical absorption in the visible spectrum. $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$ is the most promising candidate due to its superior stability, suitable direct band gap, and strong optical absorption.

4. Conclusions

In summary, the structural, mechanical, electronic and optical properties for the $\text{Cs}_2\text{Te}_{1-x}\text{Ti}_x\text{I}_6$ solid solutions have been investigated by using first-principles calculations for the first time. The calculated results show that Cs_2TeI_6 is an indirect band gap semiconductor, while Cs_2TiI_6 is a direct band gap semiconductor with the value of 0.98 eV. These compounds show good structural stability compared to $\text{CH}_3\text{NH}_3\text{PbI}_3$. An indirect-direct band gap transition can be observed when the doping concentration of Ti^{4+} is 0.50. $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$ has a suitable direct band gap (1.09 eV), which is considered as a promising photovoltaic material for single-junction solar cells. Further analysis reveals that all the structures are ductile materials except for $\text{Cs}_2\text{Te}_{0.50}\text{Ti}_{0.50}\text{I}_6$. Moreover, these materials have large optical absorption coefficients in the visible light region. We expect that this study can provide insights into

developing the stable, non-toxic, and high-efficiency perovskite materials for optoelectronic devices.

Conflicts of interest

There are no conflicts to declare.

Acknowledgements

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